mail

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





HMC636ST89 / 636ST89E

v02.0311

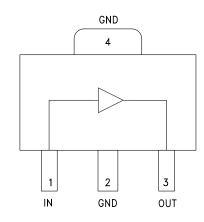


Typical Applications

The HMC636ST89(E) is ideal for:

- Cellular / PCS / 3G
- WiMAX, WiBro, & Fixed Wireless
- CATV & Cable Modem
- Microwave Radio

Functional Diagram



GaAs PHEMT HIGH LINEARITY Gain Block, 0.2 - 4.0 GHz

Features

Low Noise Figure: 2.2 dB High P1dB Output Power: +22 dBm High Output IP3: +40 dBm Gain: 13 dB 50 Ohm I/O's - No External Matching Industry Standard SOT89 Package

General Description

The HMC636ST89(E) is a GaAs pHEMT, High Linearity, Low Noise, Wideband Gain Block Amplifier covering 0.2 to 4.0 GHz. Packaged in an industry standard SOT89, the amplifier can be used as either a cascadable 50 Ohm gain stage, a PA Pre-Driver, a Low Noise Amplifier, or a Gain Block with up to +23 dBm output power. This versatile Gain Block Amplifier is powered from a single +5V supply and requires no external matching components The internally matched topology makes this amplifier compatible with virtually any PCB material or thickness.

Electrical Specifications, Vs = 5.0 V, $T_A = +25^{\circ} C$

Parameter	Min	Тур.	Max	Min.	Тур.	Max.	Units
Frequency Range	0.2 - 2.0		2.0 - 4.0			GHz	
Gain	10	13		5	10		dB
Gain Variation Over Temperature		0.01	0.02		0.01	0.02	dB/ °C
Input Return Loss		10			10		dB
Output Return Loss		13			15		dB
Reverse Isolation		22			20		dB
Output Power for 1 dB Compression (P1dB)	19	22		20	23		dBm
Output Third Order Intercept (IP3)	36	39		36	39		dBm
Noise Figure		2.5			2		dB
Supply Current (Icq)		155			155	175	mA

Note: Data taken with broadband bias tee on device output.

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.

HMC636* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

COMPARABLE PARTS

View a parametric search of comparable parts.

EVALUATION KITS

HMC636ST89 Evaluation Board

DOCUMENTATION

Application Notes

 AN-1363: Meeting Biasing Requirements of Externally Biased RF/Microwave Amplifiers with Active Bias Controllers

Data Sheet

HMC636 Data Sheet

TOOLS AND SIMULATIONS \square

• HMC636 S-Parameter

REFERENCE MATERIALS

Quality Documentation

- Package/Assembly Qualification Test Report: 3 Lead Plastic SOT89 Package (QTR: 10002 REV: 02)
- PCN: MS, QS, SOT, SOIC packages Sn/Pb plating vendor change
- Semiconductor Qualification Test Report: PHEMT-F (QTR: 2013-00269)

DESIGN RESOURCES

- HMC636 Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

DISCUSSIONS

View all HMC636 EngineerZone Discussions.

SAMPLE AND BUY

Visit the product page to see pricing options.

TECHNICAL SUPPORT

Submit a technical question or find your regional support number.

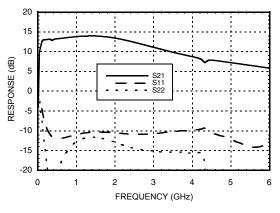
DOCUMENT FEEDBACK

Submit feedback for this data sheet.

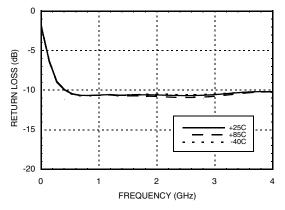




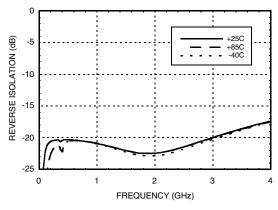
Broadband Gain & Return Loss



Input Return Loss vs. Temperature



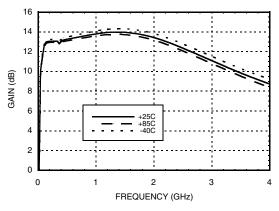
Reverse Isolation vs. Temperature



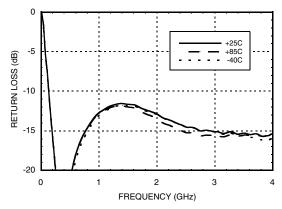
HMC636ST89 / 636ST89E

GaAs PHEMT HIGH LINEARITY Gain Block, 0.2 - 4.0 GHz

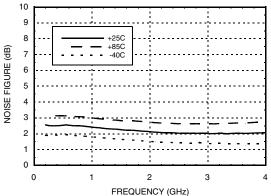
Gain vs. Temperature



Output Return Loss vs. Temperature



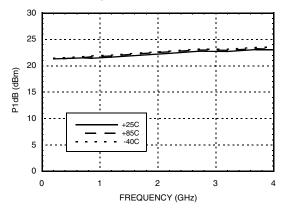
Noise Figure vs. Temperature



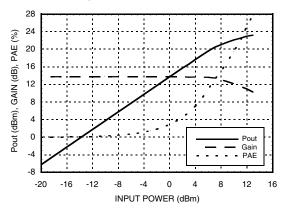




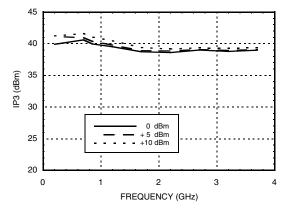
P1dB vs. Temperature



Power Compression @ 850 MHz

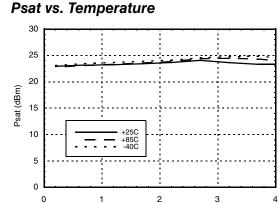


Output IP3 vs. Input Tone Power



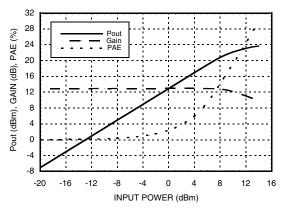
HMC636ST89 / 636ST89E

GaAs PHEMT HIGH LINEARITY Gain Block, 0.2 - 4.0 GHz

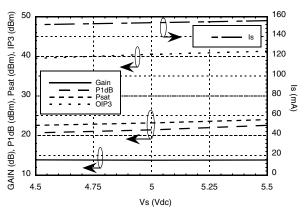




Power Compression @ 2200 MHz



Gain, Power, Output IP3 & Supply Current vs. Supply Voltage @ 850 MHz



Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.





Absolute Maximum Ratings

	•
Collector Bias Voltage (Vcc)	+5.5 Volts
RF Input Power (RFIN)(Vcc = +5 Vdc)	+16 dBm
Channel Temperature	150 °C
Continuous Pdiss (T = 85 °C) (derate 13.3 mW/°C above 85 °C)	0.86 W
Thermal Resistance (Channel to lead)	75.6 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 1A

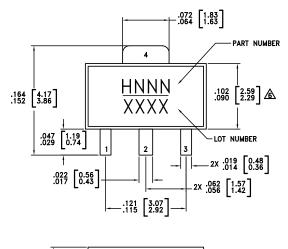


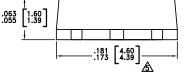
HMC636ST89 / 636ST89E

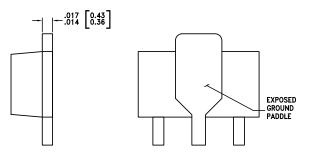
GaAs PHEMT HIGH LINEARITY

Gain Block, 0.2 - 4.0 GHz

Outline Drawing







NOTES:

1. PACKAGE BODY MATERIAL:

MOLDING COMPOUND MP-180S OR EQUIVALENT.

2. LEAD MATERIAL: Cu w/ Ag SPOT PLATING.

3. LEAD PLATING: 100% MATTE TIN.

4. DIMENSIONS ARE IN INCHES [MILLIMETERS]

DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE. DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25mm PER SIDE. 7. ALL GROUND LEADS MUST BE SOLDERED TO PCB RF GROUND.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [3]
HMC636ST89	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 ^[1]	H636 XXXX
HMC636ST89E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 ^[2]	<u>H636</u> XXXX

[1] Max peak reflow temperature of 235 °C

[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.



HMC636ST89 / 636ST89E

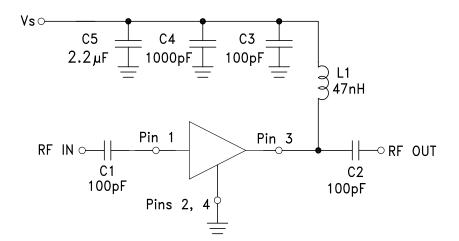
GaAs PHEMT HIGH LINEARITY Gain Block, 0.2 - 4.0 GHz



Pin Descriptions

Pin Number	Function	Description	Interface Schematic	
1	RFIN	This pin is DC coupled. An off-chip DC blocking capacitor is required.		
3	RFOUT	RF Output and DC BIAS for the amplifier. See Application Circuit for off-chip components.		
2, 4	GND	These pins and package bottom must be connected to RF/DC ground.		

Application Circuit



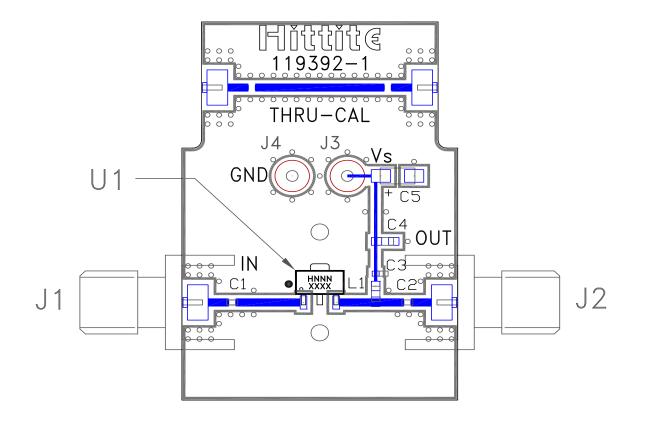


HMC636ST89 / 636ST89E

GaAs PHEMT HIGH LINEARITY Gain Block, 0.2 - 4.0 GHz



Evaluation PCB



List of Materials for Evaluation PCB 119394^[1]

Item	Description	
J1 - J2	PCB Mount SMA Connector	
J3 - J4	DC Pin	
C1 - C3	100 pF Capacitor, 0402 Pkg.	
C4	1000 pF Capacitor, 0603 Pkg.	
C5	2.2 µF Capacitor, Tantalum	
L1	47 nH Inductor, 0603 Pkg.	
U1	HMC636ST89(E)	
PCB [2]	119392 Evaluation PCB	

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: FR4

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and package bottom should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

to be accurate and reliable. However, no nor for any infringements of patents or other instance subject to chance without poice. No One Technology Way, P.O. Box 9106,

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.